

IN THE CLAIMS:

Claims 1-3 have been amended herein. All of the pending claims 1 through 3 are presented below. This listing of claims will replace all prior versions and listings in the application. Please enter these claims as amended.

1. (Currently Amended) A semiconductor wafer having a plurality of semiconductor devices formed thereon comprising:

a portion of a silicon semiconductor wafer substrate, ~~said the portion of-a the silicon~~

semiconductor wafer substrate having a first side, a second side and a plurality of street areas thereon forming areas on the portion of-a ~~the~~ silicon semiconductor wafer substrate within which a semiconductor device is located, the portion of-a ~~the~~ silicon semiconductor wafer substrate having portions thereof removed through ~~the~~ a thickness thereof in the plurality of street areas thereof;

at least two semiconductor devices formed on the first side of the portion of-a ~~the~~ silicon semiconductor wafer substrate, the at least two semiconductor devices each having a periphery having a street area of the plurality of street areas extending therefrom, the at least two semiconductor devices each having at least one bond pad formed thereon, the at least two semiconductor devices each formed on the portion of-a ~~the~~ silicon semiconductor wafer substrate having portions of the silicon semiconductor wafer substrate removed from the plurality of street areas of the portion of a silicon semiconductor wafer substrate, the at least two semiconductor devices each having areas, the periphery of each of the at least two semiconductor devices thereof formed by the portions of the silicon semiconductor wafer substrate removed in from the plurality of street areas of the portion of a silicon semiconductor wafer substrate;

a first coating comprised of glass covering the first side of the portion of-a ~~the~~ silicon semiconductor wafer substrate and the at least two semiconductor devices formed on the first side of the portion of-a ~~the~~ silicon semiconductor wafer substrate, the first coating sealingly engaging the first side of the portion of-a ~~the~~ silicon semiconductor wafer

substrate, the first coating on the first side of the portion of a silicon semiconductor wafer substrate covering the at least two semiconductor devices formed thereon without substantially covering the at least one bond pad formed thereon; a second coating comprising a removable glass material covering the second side of the portion of-a~~the~~ silicon semiconductor wafer substrate and substantially filling the portions of~~the street areas of the portion of a~~the silicon semiconductor wafer substrate which have been removed~~-separating to separate~~ areas of the portion of-a~~the~~ silicon semiconductor wafer substrate from other areas thereof, the second coating contacting the first coating in the portions of~~the street areas of the portion of a~~the silicon semiconductor wafer substrate which have been removed, the second coating substantially sealingly engaging the periphery of each of the at least two semiconductor devices; and a plurality of metal circuits ~~being~~ connected to the at least one bond pad of each of the at least two semiconductor devices, the at least one metal circuit extending to a location adjacent the periphery of each of the at least two semiconductor devices, the ~~at least one~~ plurality of ~~metal~~ circuit circuits sealingly engaging the first coating on the portion of-a~~the~~ silicon semiconductor wafer substrate and the at least one bond pad of each of the at least two semiconductor devices.

2. (Currently Amended) The ~~portion of a~~ semiconductor wafer of claim 1, wherein: the second coating comprises a glass coating which is etchable.

3. (Currently Amended) The ~~portion of a~~ semiconductor wafer of claim 1, further comprising:
a plurality of metal circuits located on the first coating on the first side of the portion of-a~~the~~ silicon semiconductor wafer substrate.